

depositing a material further comprises plasma-depositing a material comprising carbon and hydrogen, and wherein said step of plasma-depositing a material further comprises plasma-depositing a halogen-free material.

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Cent 41. (Once amended) A method of developing an in-process semiconductor device having a first metal line and a second metal line, comprising:

placing said device in a deposition and etch surrounding;
forming a polymer between said first metal line and said second metal line
providing a layer over said polymer; and
retaining a state of said polymer.

A marked version of these claims appears in an appendix to this Amendment and response.

REMARKS

Claims 1-8, 10-14, 19, 23-24, 29-32, and 36-43 were pending up to this Amendment and Response.

Claims 1-8, 10-14, 19, 23-24, 29-32, and 36-40 are rejected.

Claims 1-8, 10, 12-14, 19, 23-24, 29-32, and 36-40 are cancelled without prejudice.

Claims 41-43 are objected to.

Claims 11 and 41 are amended.

Claims 11 and 41-43 are pending as a result of this Amendment and Response.

I. Rejected claims

The Examiner rejected claims 11 and 12 under §112 ¶2 due to a perceived conflict in their respective limitations. Applicants have cancelled claim 12 in order to address its

§102 rejection in a related application. With the cancellation of claim 12, Applicants contend that there is no substantive basis for rejecting claim 11. Accordingly, Applicants have amended claim 11 to independent form by expressly incorporating the limitations in claims 7 and 10.

The Examiner rejected claims 1-8, 10, 12-14, 19, 23-24, 29-32, and 36-40 under §102 in light of Japanese Pat. No. 06-275568. Applicants have cancelled these claims in the interest of publishing the objected claims. However, Applicants intend to further pursue these cancelled claims in a continuation application. Applicants will bear in mind the Examiner's comments regarding those claims. Accordingly, Applicants request that claims 1-8, 10, 12-14, 19, 23-24, 29-32, and 36-40 be cancelled without prejudice.

II. Objected claims

The Examiner objected to claims 41-43 as being dependent upon a rejected base claim. Accordingly, Applicants have amended claim 41 to independent form by expressly incorporating the limitations in claim 40.

Conclusion

In light of the above amendments and remarks, Applicants submit that claims 11 and 41-43 are allowable over the Examiner's objection and rejection. Therefore, Applicants respectfully request allowance of all of the pending claims. Please address further correspondence with this application to: Charles B. Brantley, II, Micron Technology, Inc., Mail Stop 525, 8000 S. Federal Way, Boise, ID 83706-9632, telephone number (208) 368-4557.

MICRON, TECHNOLOGY, INC.

Date 7/15/83

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Appendix: Marked version of amended claims

11. (Once amended) [The method in claim 10] A method of processing a semiconductor device, comprising:

providing a first protruding feature on a layer of said semiconductor device;

providing a second protruding feature on said layer;

defining a recess between said first protruding feature and said second protruding feature; and

plasma-depositing a material within said recess, wherein said step of plasma-depositing a material further comprises plasma-depositing a material comprising carbon and hydrogen, and wherein said step of plasma-depositing a material further comprises plasma-depositing a halogen-free material.

41. (Once amended) [The method in claim 40, further comprising:] A method of developing an in-process semiconductor device having a first metal line and a second metal line, comprising:

placing said device in a deposition and etch surrounding;

forming a polymer between said first metal line and said second metal line

providing a layer over said polymer; and

retaining a state of said polymer.